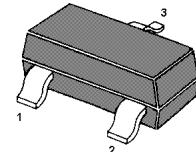


BCW30 PNP Silicon Epitaxial Planar Transistor

general purpose switching and amplification



1.Base 2.Emitter 3.Collector
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{\text{CBO}}$	32	V
Collector Emitter Voltage	$-V_{\text{CEO}}$	32	V
Emitter Base Voltage	$-V_{\text{EBO}}$	5	V
Collector Current	$-I_C$	100	mA
Peak Collector Current	$-I_{\text{CM}}$	200	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_s	- 55 to + 150	$^\circ\text{C}$

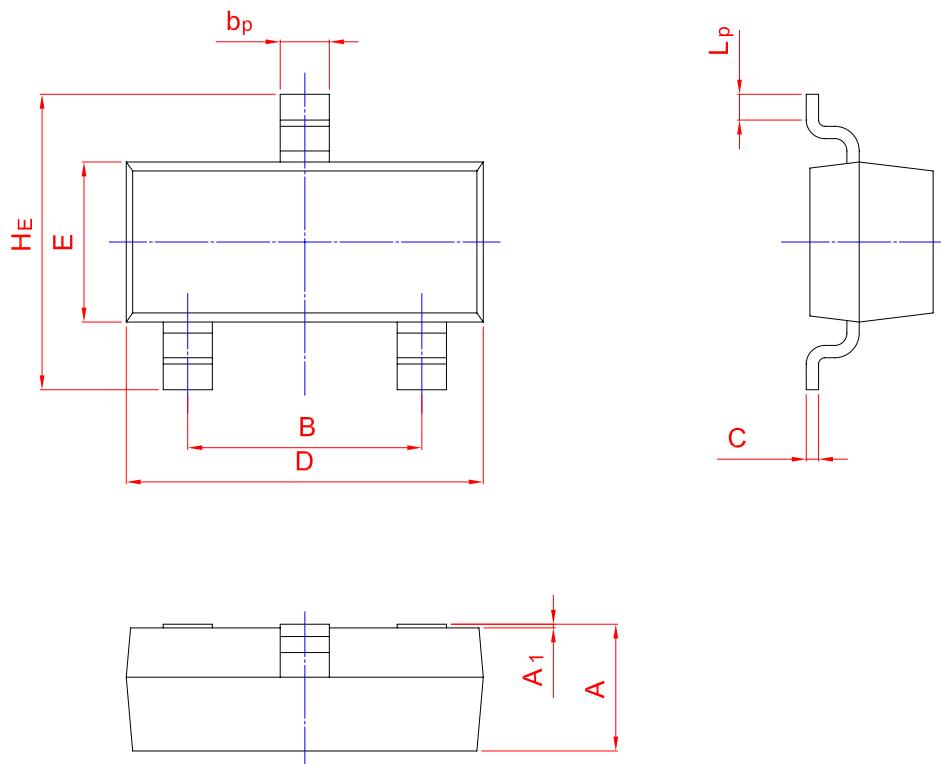
Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{\text{CE}} = 5 \text{ V}$, $-I_C = 2 \text{ mA}$	h_{FE}	215	-	500	-
Collector Cutoff Current at $-V_{\text{CB}} = 30 \text{ V}$	$-I_{\text{CBO}}$	-	-	100	nA
Emitter Cutoff Current at $-V_{\text{EB}} = 5 \text{ V}$	$-I_{\text{EBO}}$	-	-	100	nA
Collector Base Breakdown Voltage at $-I_C = 10 \mu\text{A}$	$-V_{(\text{BR})\text{CBO}}$	32	-	-	V
Collector Emitter Breakdown Voltage at $-I_C = 1 \text{ mA}$	$-V_{(\text{BR})\text{CEO}}$	32	-	-	V
Emitter Base Breakdown Voltage at $-I_E = 10 \mu\text{A}$	$-V_{(\text{BR})\text{EBO}}$	5	-	-	V
Collector Emitter Saturation Voltage at $-I_C = 10 \text{ mA}$, $-I_B = 0.5 \text{ mA}$	$-V_{\text{CE}(\text{sat})}$	-	-	0.3	V
Base Emitter Voltage at $-V_{\text{CE}} = 5 \text{ V}$, $-I_C = 2 \text{ mA}$	$-V_{\text{BE}}$	0.6	-	0.75	V
Transition Frequency at $-V_{\text{CE}} = 5 \text{ V}$, $I_E = 10 \text{ mA}$, $f = 100 \text{ MHz}$	f_T	100	-	-	MHz
Collector Base Capacitance at $-V_{\text{CB}} = 10 \text{ V}$, $f = 1 \text{ MHz}$	C_{CBO}	-	4.5	-	pF

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	b_p	C	D	E	H_E	A_1	L_p
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20